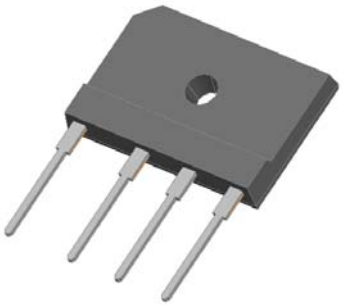
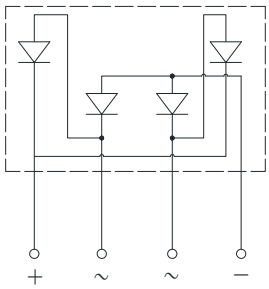
Low VF Bridge Rectifiers





Features

- based on silicon planar process
- Low VF
- Thin single in-line package
- High surge current capability
- Solder dip 275 °C max. 7 s, per JESD 22-B106

Typical Applications

General purpose use in AC/DC bridge full wave rectification for switching power supply, home appliances, office equipment, industrial automation applications.

Mechanical Data

- **Package**: 6KBJ
  Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant
- **Terminals**: Tin plated leads, solderable per J-STD-002 and JESD22-B102
- **Polarity:** As marked on body

■Maximum Ratings (T_a=25℃ Unless otherwise specified）

PARAMETER		SYMBOL	UNIT	GBJU2506
Device marking code				GBJU2506
Maximum Repetitive Peak Reverse Voltage		V_{RRM}	V	600
Maximum RMS Voltage		V_{RMS}	V	420
Maximum DC blocking Voltage		V_{DC}	V	600
Average rectified output current @60Hz sine wave, R-load	With heatsink Tc =115℃	I_O	A	25.0
	Without heatsink Ta =25℃			4.5
Forward Surge Current (Non-repetitive) @60Hz Half-sine wave,1 cycle, Tj=25℃		I_{FSM}	A	360
Forward Surge Current (Non-repetitive) @1ms, square wave, 1 cycle, Tj=25℃				720
Current squared time @1ms≤t≤8.3ms Tj=25℃, Rating of per diode		I^2t	A^2S	538
Storage temperature		T_{stg}	℃	-55 ~ +150
Junction temperature		T_j	℃	-55 ~ +150
Dielectric strength @ Terminals to case, AC 1 minute		V_{dis}	KV	2.5
Mounting torque @Recommend torque：5kg·cm		Tor	kg·cm	8

■Electrical Characteristics（T_a=25℃ Unless otherwise specified）

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	Min	Typ	Max
Instantaneous forward voltage drop per diode	V_F	V	I_{FM}=12.5A	0.80	0.875	0.92
DC reverse current at rated DC blocking voltage per diode	I_R	μA	T_j=25℃	-	0.001	5
			T_j=125℃	-	-	50
Junction capacitance	Cj	pF	Measured at 1MHz and Applied Reverse Voltage of 4.0 V.D.C	150	185	250

■Thermal Characteristics （T_a=25℃ Unless otherwise specified）

PARAMETER		SYMBOL	UNIT	GBJU2506
Typical Thermal Resistance	Between junction and ambient, Without heatsink	RθJ-A	℃/W	18.0
	Between junction and case, With heatsink	RθJ-C		0.8
	Between junction and Lead With heatsink	RθJ-L		5.0

Note: Device mounted on 75mm x 45mm x 5.5mm Aluminum Plate Heatsink.

■Ordering Information (Example)

PREFERED P/N	PACKING CODE	UNIT WEIGHT(g)	MINIIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
GBJU2506	B1	Approximate 6.5	15	750	1500	TUBE

■ Characteristics(Typical)

FIG1:Io-Tc Curve

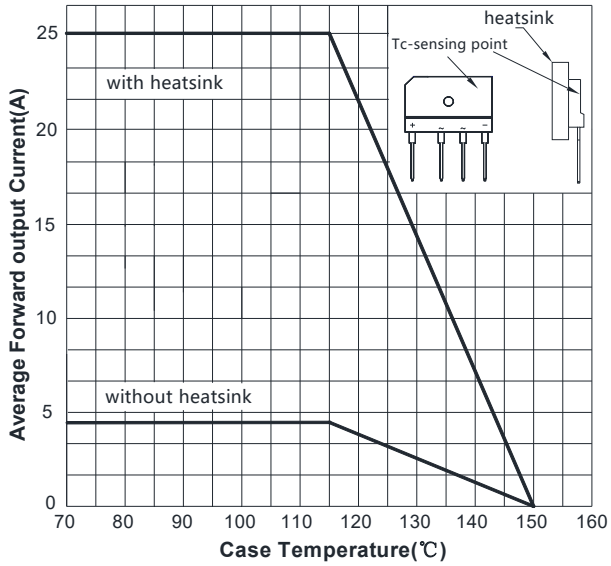
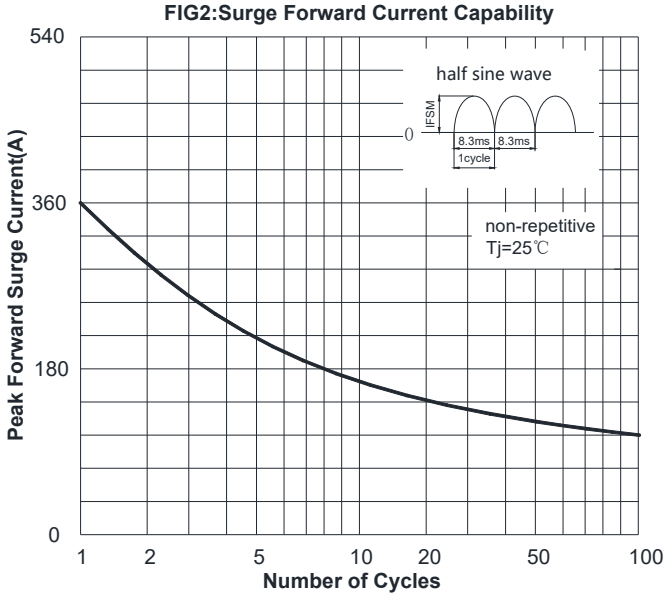
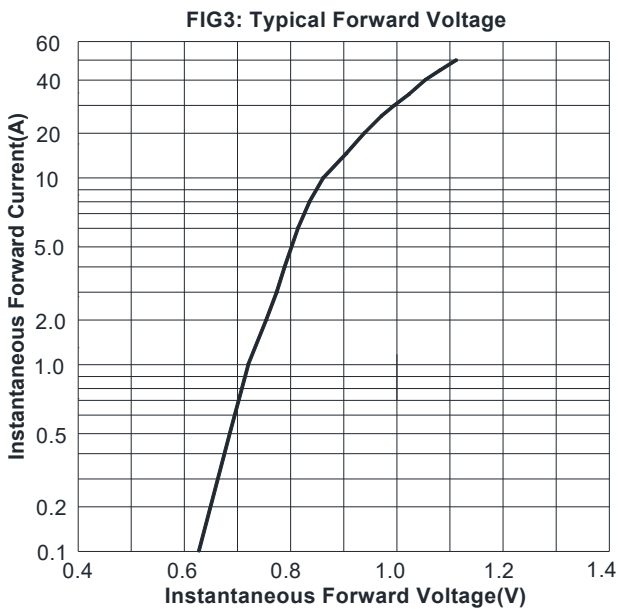
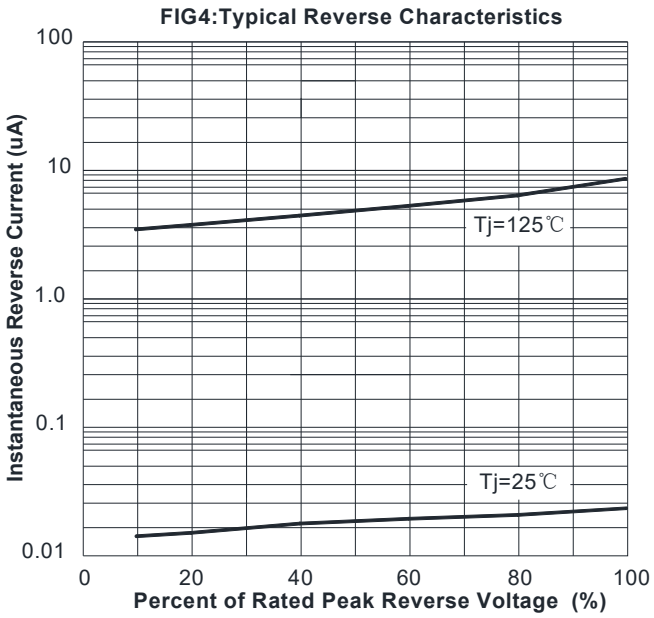


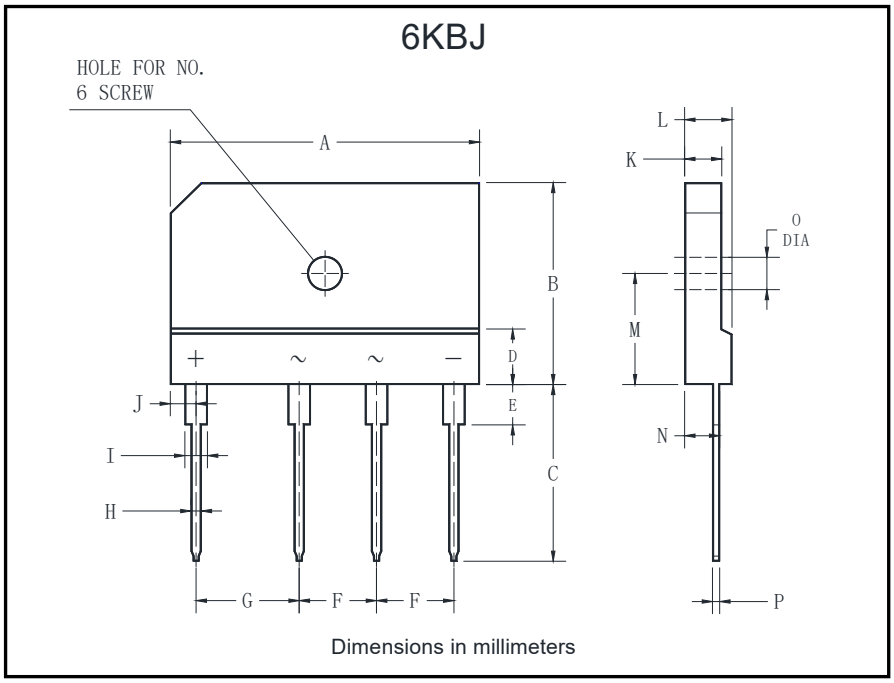
FIG2:Surge Forward Current Capability







■ Outline Dimensions



6KBJ		
Dim	Min	Max
A	29.7	30.3
B	19.7	20.3
C	17.0	18.0
D	4.8	5.8
E	3.8	4.2
F	7.3	7.7
G	9.8	10.2
H	0.9	1.1
I	2.0	2.4
J	2.3	2.7
K	3.4	3.8
L	4.4	4.8
M	10.8	11.2
N	3.1	3.7
O	3.1	3.4
P	0.6	0.8

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